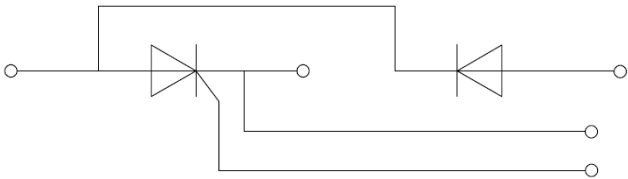




°C		



	°C			
				°C
				°C

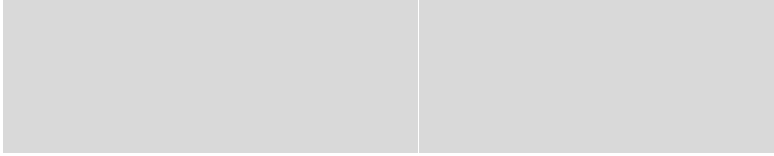




FIG.1: Power dissipation vs. on-state current
(per thyristor or diode)

$P_T(AV)/P_F(AV)(W)$

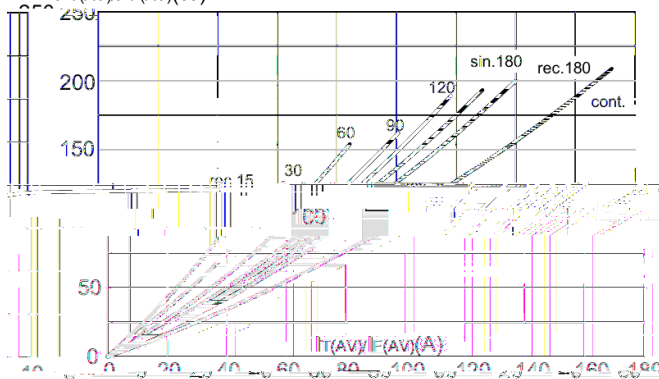


FIG.2: Maximum transient thermal impedance
junction to case(per thyristor or diode)

$R_{th(j-c)}(^{\circ}C/W)$

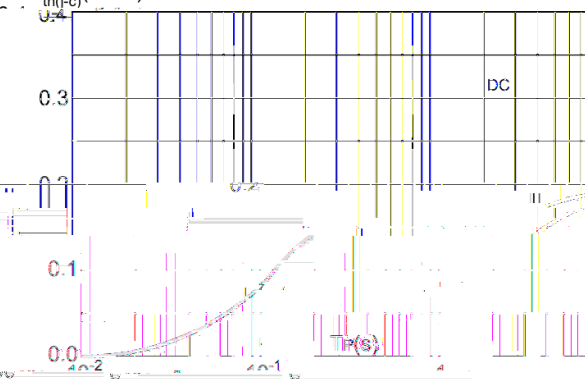


FIG.3: Forward characteristics

FIG.4: Relative variations of gate trigger current, holding

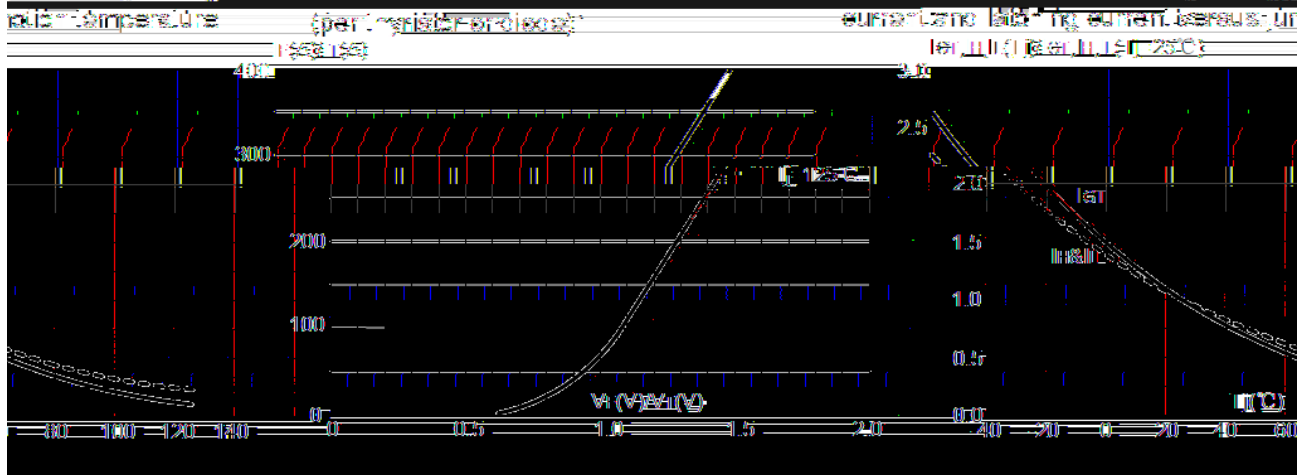


FIG.5 Gate trigger characteristics

FIG.6: Forward current vs. case temperature
(per thyristor or diode)



